

<IGBT Modules>

CM200DX-34SA

HIGH POWER SWITCHING USE
INSULATED TYPE



dual switch (half-bridge)

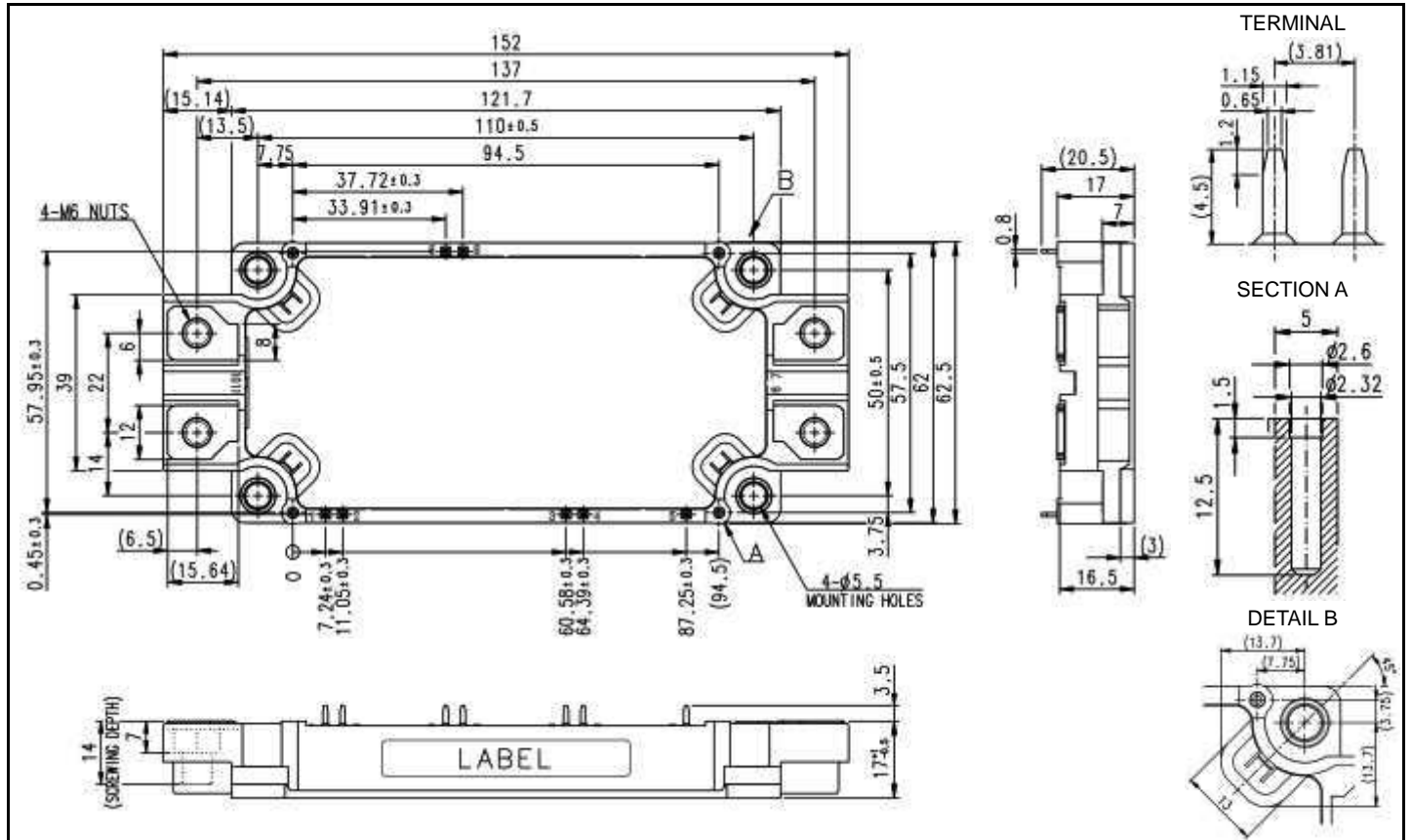
Collector current I_C **200 A**
 Collector-emitter voltage V_{CES} **1700 V**
 Maximum junction temperature T_{vjmax} **175 °C**

- Flat base type
- Copper base plate (non-plating)
- RoHS Directive compliant
- Tin-plating pin terminals
- UL Recognized under UL1557, File No. E323585

APPLICATION

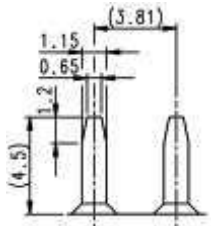
AC Motor Control, Motion/Servo Control, Power supply, etc.

OUTLINE DRAWING

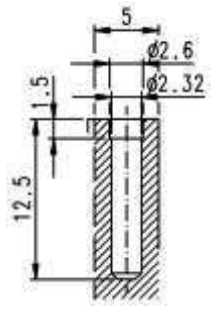


Dimension in mm

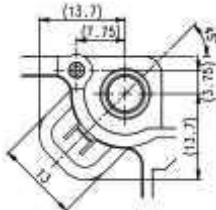
TERMINAL



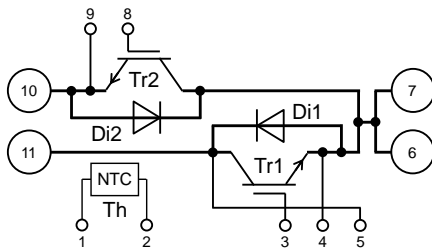
SECTION A



DETAIL B



INTERNAL CONNECTION



Terminal code

- | | |
|--------|---------|
| 1. TH1 | 6. C2E1 |
| 2. TH2 | 7. C2E1 |
| 3. G1 | 8. G2 |
| 4. Es1 | 9. Es2 |
| 5. Cs1 | 10. E2 |
| | 11. C1 |

Tolerance otherwise specified

Division of Dimension	Tolerance
0.5 to 3	±0.2
over 3 to 6	±0.3
over 6 to 30	±0.5
over 30 to 120	±0.8
over 120 to 400	±1.2

CM200DX-34SA

HIGH POWER SWITCHING USE
INSULATED TYPEMAXIMUM RATINGS ($T_{vj}=25\text{ }^{\circ}\text{C}$, unless otherwise specified)

INVERTER PART IGBT/FWD

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	1700	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I_C	Collector current	DC, $T_C=125\text{ }^{\circ}\text{C}$ (Note2, 4)	200	A
I_{CRM}		Pulse, Repetitive (Note3)	400	
P_{tot}	Total power dissipation	$T_C=25\text{ }^{\circ}\text{C}$ (Note2, 4)	2000	W
I_E (Note1)	Emitter current	DC (Note2)	200	A
I_{ERM} (Note1)		Pulse, Repetitive (Note3)	400	

MODULE

Symbol	Item	Conditions	Rating	Unit
V_{isol}	Isolation voltage	Terminals to base plate, RMS, $f=60\text{ Hz}$, AC 1 min	4000	V
T_{vjmax}	Maximum junction temperature	Instantaneous event (overload)	175	$^{\circ}\text{C}$
T_{Cmax}	Maximum case temperature	(Note4)	125	
T_{vjop}	Operating junction temperature	Continuous operation (under switching)	-40 ~ +150	$^{\circ}\text{C}$
T_{stg}	Storage temperature	-	-40 ~ +125	

ELECTRICAL CHARACTERISTICS ($T_{vj}=25\text{ }^{\circ}\text{C}$, unless otherwise specified)

INVERTER PART IGBT/FWD

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I_{CES}	Collector-emitter cut-off current	$V_{CE}=V_{CES}$, G-E short-circuited	-	-	1.0	mA	
I_{GES}	Gate-emitter leakage current	$V_{GE}=V_{GES}$, C-E short-circuited	-	-	0.5	μA	
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=20\text{ mA}$, $V_{CE}=10\text{ V}$	5.4	6.0	6.6	V	
V_{CEsat} (Terminal)	Collector-emitter saturation voltage	$I_C=200\text{ A}$, $V_{GE}=15\text{ V}$, Refer to the figure of test circuit (Note5)	$T_{vj}=25\text{ }^{\circ}\text{C}$	-	2.00	2.50	V
			$T_{vj}=125\text{ }^{\circ}\text{C}$	-	2.20	-	
			$T_{vj}=150\text{ }^{\circ}\text{C}$	-	2.25	-	
V_{CEsat} (Chip)		$I_C=200\text{ A}$, $V_{GE}=15\text{ V}$, (Note5)	$T_{vj}=25\text{ }^{\circ}\text{C}$	-	1.90	2.40	V
			$T_{vj}=125\text{ }^{\circ}\text{C}$	-	2.10	-	
			$T_{vj}=150\text{ }^{\circ}\text{C}$	-	2.15	-	
C_{ies}	Input capacitance	$V_{CE}=10\text{ V}$, G-E short-circuited	-	-	53	nF	
C_{oes}	Output capacitance		-	-	4.3		
C_{res}	Reverse transfer capacitance		-	-	0.97		
Q_G	Gate charge	$V_{CC}=1000\text{ V}$, $I_C=200\text{ A}$, $V_{GE}=15\text{ V}$	-	1100	-	nC	
$t_{d(on)}$	Turn-on delay time	$V_{CC}=1000\text{ V}$, $I_C=200\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\text{ }\Omega$, Inductive load	-	-	400	ns	
t_r	Rise time		-	-	100		
$t_{d(off)}$	Turn-off delay time		-	-	700		
t_f	Fall time		-	-	600		
V_{EC} (Note1) (Terminal)	Emitter-collector voltage	$I_E=200\text{ A}$, G-E short-circuited, Refer to the figure of test circuit (Note5)	$T_{vj}=25\text{ }^{\circ}\text{C}$	-	4.1	5.3	V
			$T_{vj}=125\text{ }^{\circ}\text{C}$	-	2.9	-	
			$T_{vj}=150\text{ }^{\circ}\text{C}$	-	2.7	-	
V_{EC} (Note1) (Chip)		$I_E=200\text{ A}$, G-E short-circuited, (Note5)	$T_{vj}=25\text{ }^{\circ}\text{C}$	-	4.0	5.2	V
			$T_{vj}=125\text{ }^{\circ}\text{C}$	-	2.8	-	
			$T_{vj}=150\text{ }^{\circ}\text{C}$	-	2.6	-	
t_{rr} (Note1)	Reverse recovery time	$V_{CC}=1000\text{ V}$, $I_E=200\text{ A}$, $V_{GE}=\pm 15\text{ V}$,	-	-	300	ns	
Q_{rr} (Note1)	Reverse recovery charge	$R_G=0\text{ }\Omega$, Inductive load	-	8.0	-	μC	
E_{on}	Turn-on switching energy per pulse	$V_{CC}=1000\text{ V}$, $I_C=I_E=200\text{ A}$,	-	28	-	mJ	
E_{off}	Turn-off switching energy per pulse	$V_{GE}=\pm 15\text{ V}$, $R_G=0\text{ }\Omega$, $T_{vj}=150\text{ }^{\circ}\text{C}$,	-	52	-		
E_{rr} (Note1)	Reverse recovery energy per pulse	Inductive load	-	42	-	mJ	
$R_{CC'+EE'}$	Internal lead resistance	Main terminals-chip, per switch, $T_C=25\text{ }^{\circ}\text{C}$ (Note4)	-	-	1.2	m Ω	
r_g	Internal gate resistance	Per switch	-	2.5	-	Ω	

CM200DX-34SA

HIGH POWER SWITCHING USE
INSULATED TYPE

ELECTRICAL CHARACTERISTICS (cont.; T_{vj}=25 °C, unless otherwise specified) NTC THERMISTOR PART

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R ₂₅	Zero-power resistance	T _C =25 °C (Note4)	4.85	5.00	5.15	kΩ
ΔR/R	Deviation of resistance	R ₁₀₀ =493 Ω, T _C =100 °C (Note4)	-7.3	-	+7.8	%
B _(25/50)	B-constant	Approximate by equation (Note6)	-	3375	-	K
P ₂₅	Power dissipation	T _C =25 °C (Note4)	-	-	10	mW

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R _{th(j-c)Q}	Thermal resistance	Junction to case, per Inverter IGBT (Note4)	-	-	75	K/kW
R _{th(j-c)D}		Junction to case, per Inverter FWD (Note4)	-	-	120	
R _{th(c-s)}	Contact thermal resistance	Case to heat sink, Thermal grease applied (Note4, 7) per 1 module,	-	15	-	K/kW

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M _t	Mounting torque	Main terminals M 6 screw	3.5	4.0	4.5	N·m
M _s	Mounting torque	Mounting to heat sink M 5 screw	2.5	3.0	3.5	N·m
d _s	Creepage distance	Terminal to terminal	17	-	-	mm
		Terminal to base plate	18.5	-	-	
d _a	Clearance	Terminal to terminal	10	-	-	mm
		Terminal to base plate	16.3	-	-	
e _c	Flatness of base plate	On the centerline X, Y (Note8)	±0	-	+100	μm
m	mass	-	-	350	-	g

*: This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free-wheeling diode (FWD).

- Junction temperature (T_{vj}) should not increase beyond T_{vjmax} rating.
- Pulse width and repetition rate should be such that the device junction temperature (T_{vj}) dose not exceed T_{vjmax} rating.
- Case temperature (T_C) and heat sink temperature (T_S) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.
- Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.

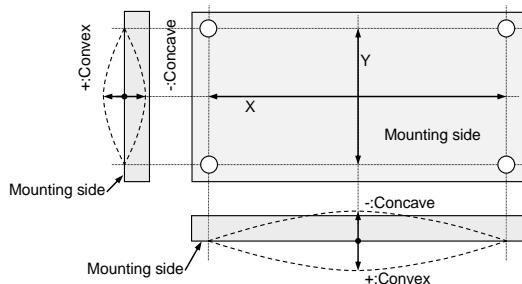
$$B_{(25/50)} = \ln\left(\frac{R_{25}}{R_{50}}\right) / \left(\frac{1}{T_{25}} - \frac{1}{T_{50}}\right)$$

R₂₅: resistance at absolute temperature T₂₅ [K]; T₂₅=25 [°C]+273.15=298.15 [K]

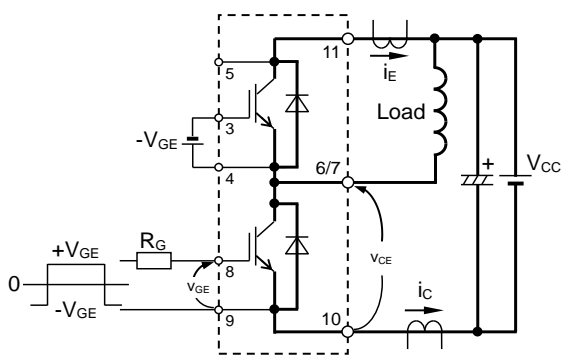
R₅₀: resistance at absolute temperature T₅₀ [K]; T₅₀=50 [°C]+273.15=323.15 [K]

7. Typical value is measured by using thermally conductive grease of λ=0.9 W/(m·K)/D_(C-S)=50 μm.

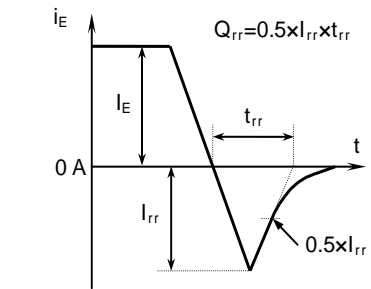
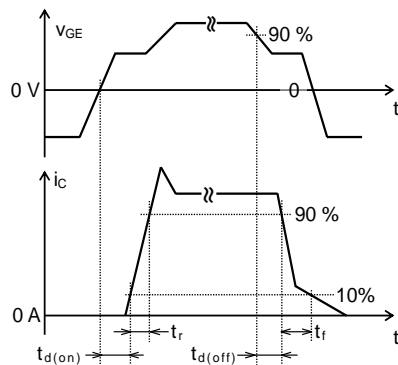
8. The base plate (mounting side) flatness measurement points (X, Y) are shown in the following figure.



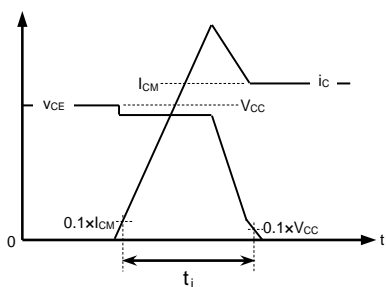
TEST CIRCUIT AND WAVEFORMS



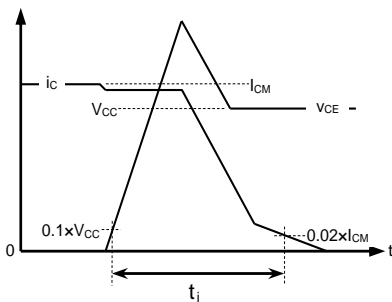
Switching characteristics test circuit and waveforms



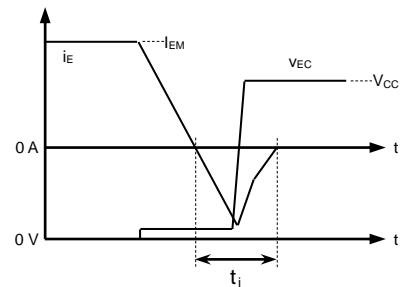
trr, Qrr characteristics test waveform



IGBT Turn-on switching energy



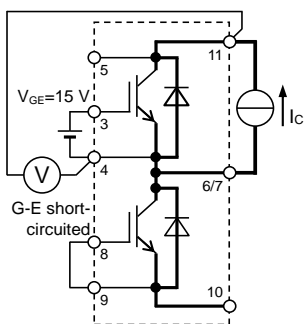
IGBT Turn-off switching energy



FWD Reverse recovery energy

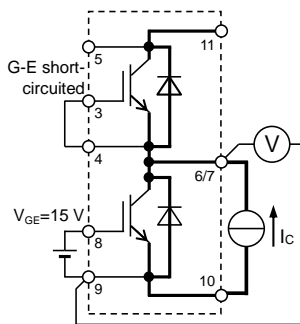
Switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

TEST CIRCUIT

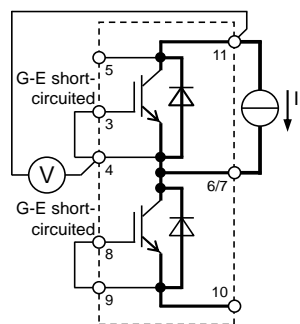


Tr1

V_{CEsat} characteristics test circuit

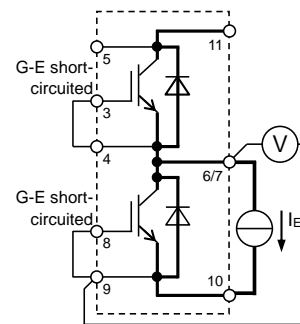


Tr2



Di1

V_{EC} characteristics test circuit



Di2

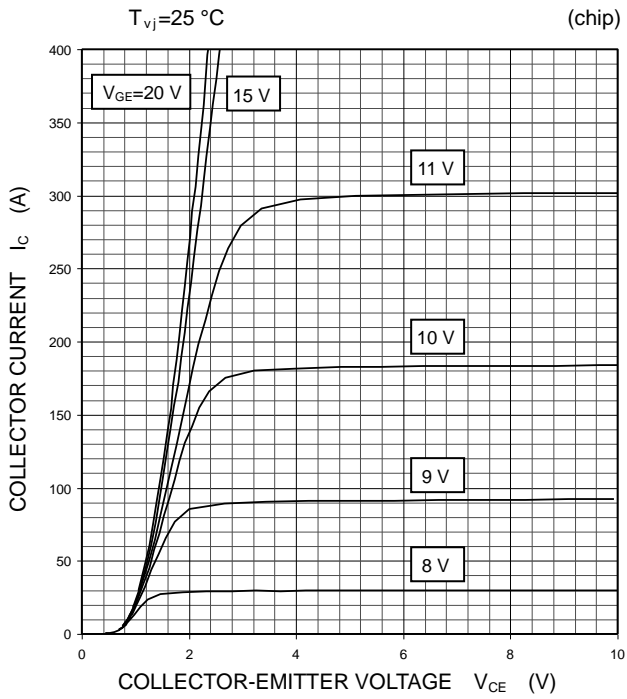
CM200DX-34SA

HIGH POWER SWITCHING USE
INSULATED TYPE

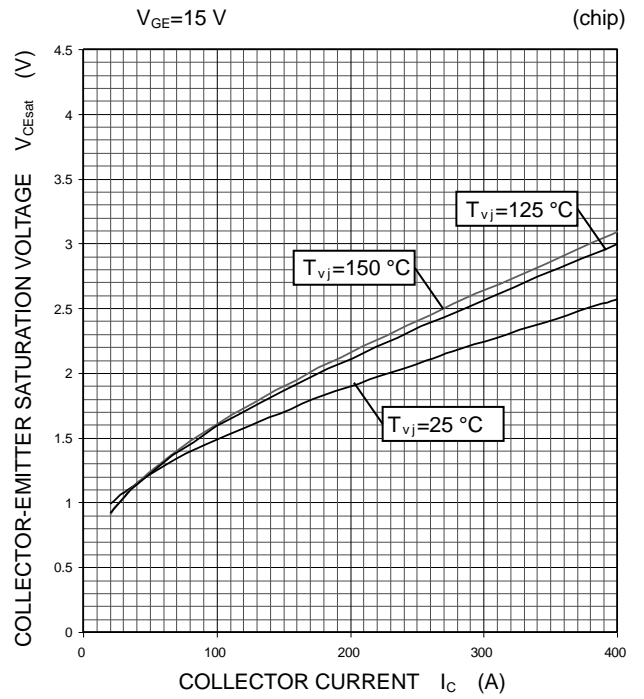
PERFORMANCE CURVES

INVERTER PART

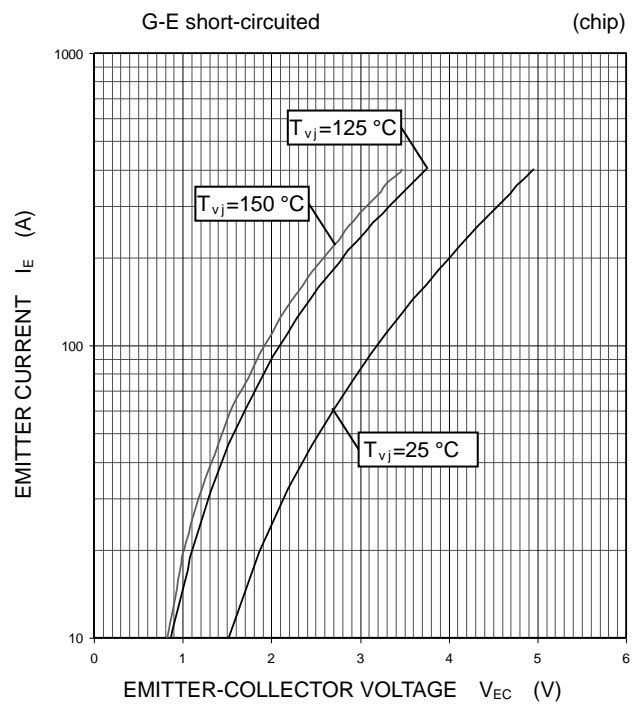
OUTPUT CHARACTERISTICS
(TYPICAL)



COLLECTOR-EMITTER SATURATION VOLTAGE
CHARACTERISTICS
(TYPICAL)



FREE WHEELING DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



CM200DX-34SA

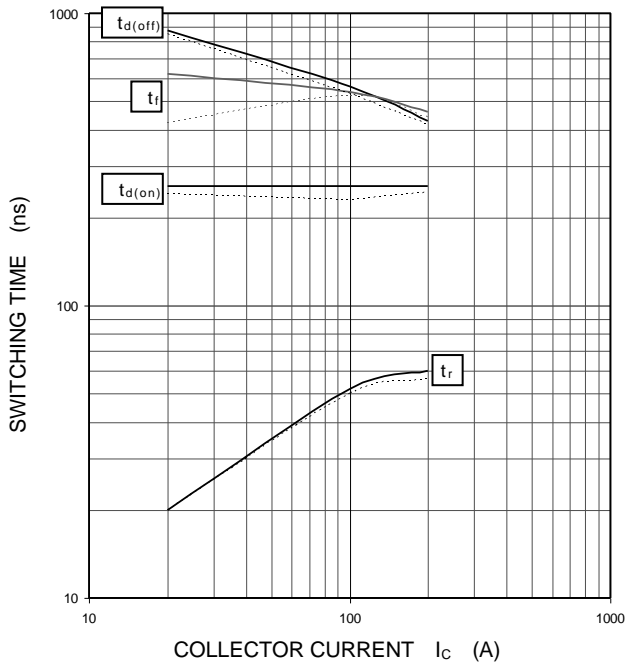
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

INVERTER PART

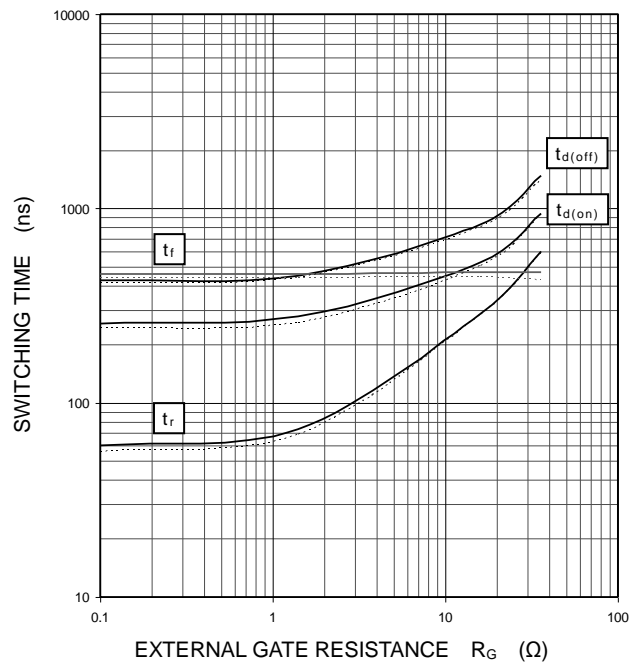
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=1000\text{ V}$, $R_G=0\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



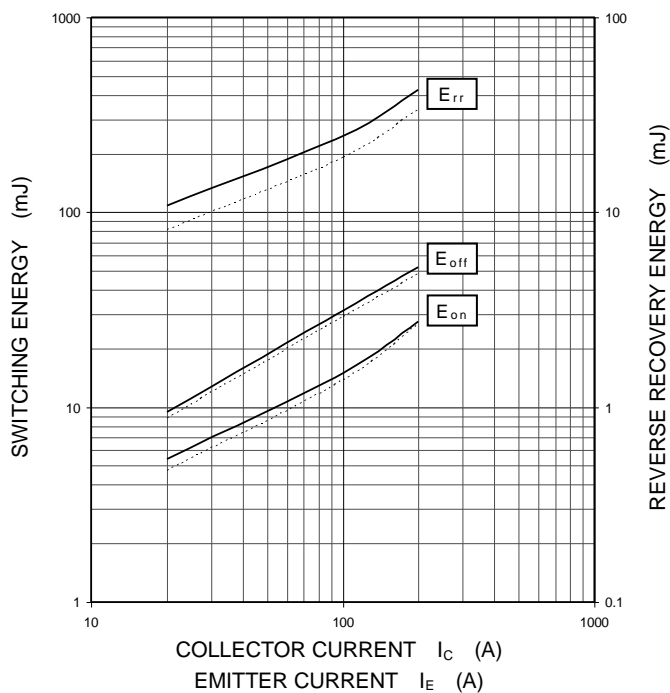
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=1000\text{ V}$, $I_C=200\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



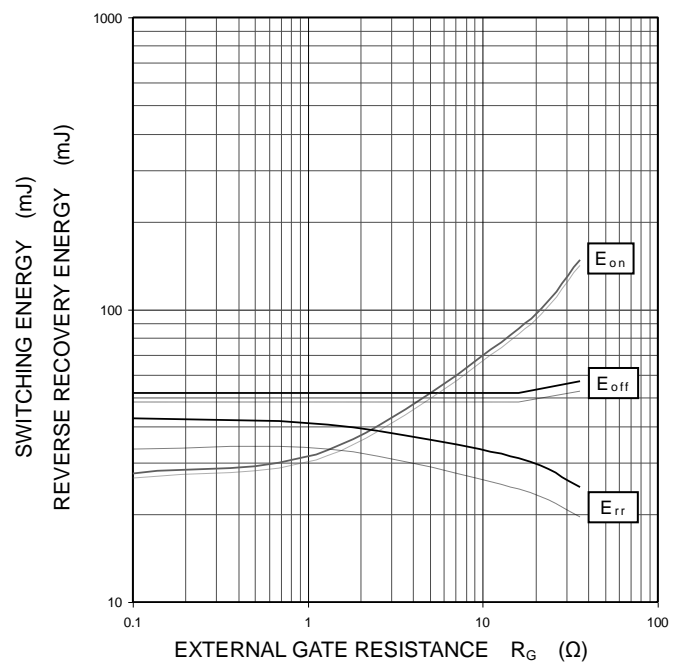
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=1000\text{ V}$, $R_G=0\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD,
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$, PER PULSE



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=1000\text{ V}$, $I_C/I_E=200\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD,
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$, PER PULSE



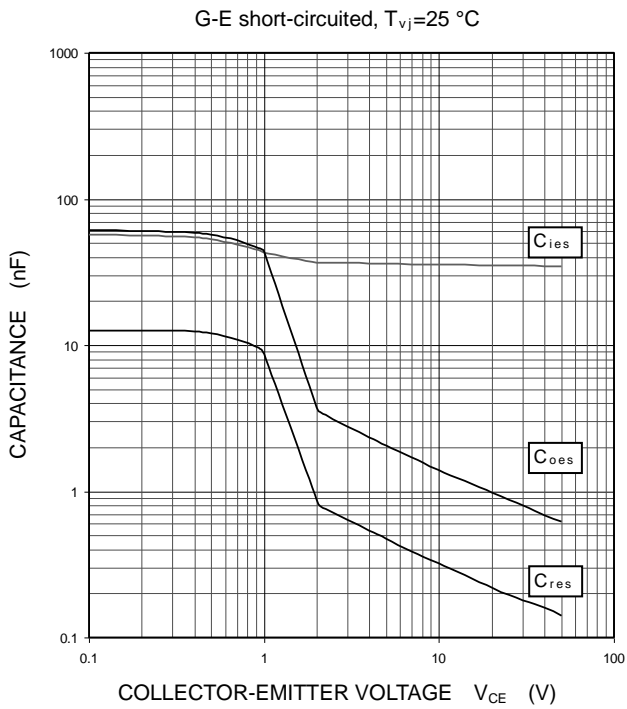
CM200DX-34SA

HIGH POWER SWITCHING USE
INSULATED TYPE

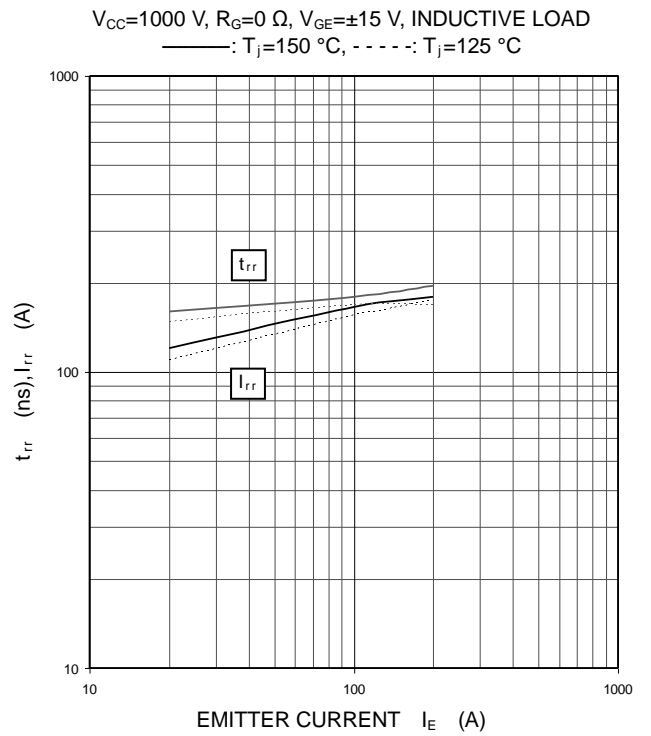
PERFORMANCE CURVES

INVERTER PART

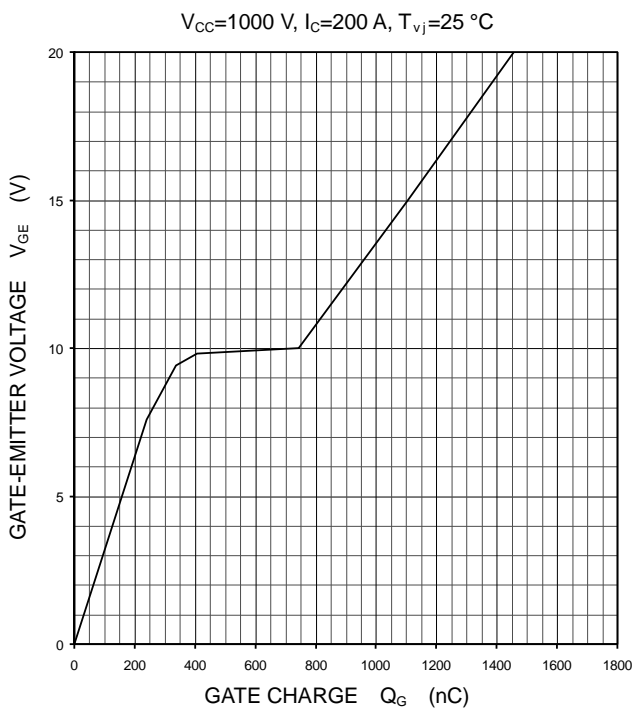
CAPACITANCE CHARACTERISTICS (TYPICAL)



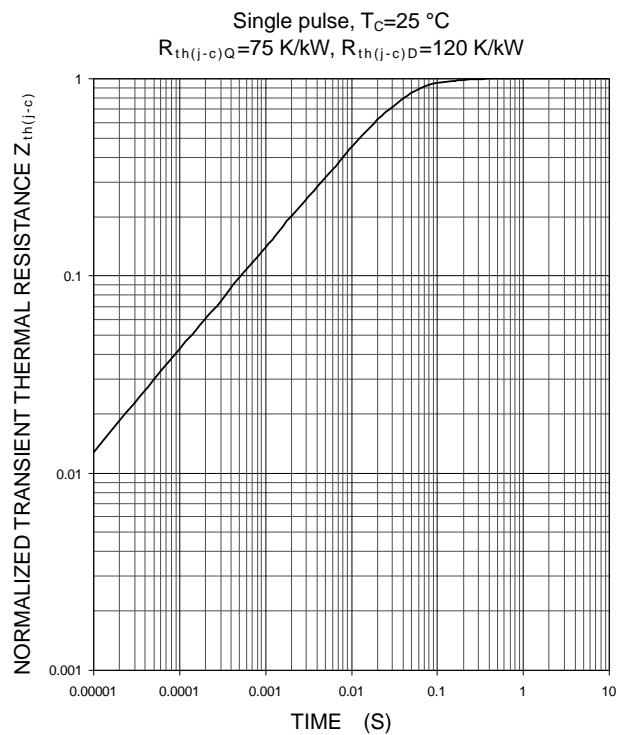
FREE WHEELING DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



GATE CHARGE CHARACTERISTICS (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)

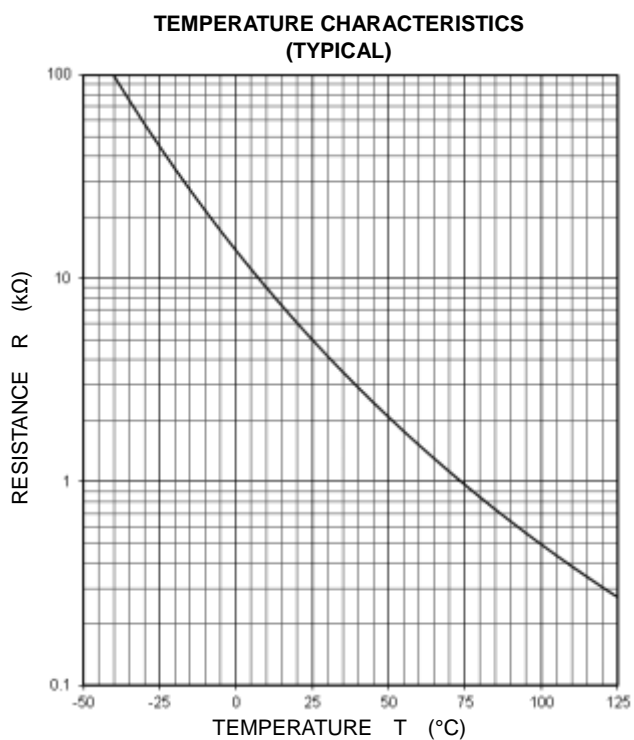


CM200DX-34SA

HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

NTC thermistor part



Note: The characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Keep safety first in your circuit designs!

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